

ABSTRACT OF THE DISCLOSURE

The present invention provides a metallization structure for semiconductor device interconnects such as a conductive line, including a substrate with a substantially planar upper surface, foundation metal layer disposed on a portion of the substrate upper surface, primary conducting metal layer overlying the foundation metal layer, and metal spacer on the sidewalls of the primary conducting metal layer and the foundation metal layer. The present invention also provides a metallization structure including a substrate with a foundation metal layer disposed thereon, a dielectric layer with an aperture therethrough being disposed on the substrate, where the bottom of the aperture exposes the foundation metal layer of the substrate, and a metal spacer on the sidewall of the aperture and a line or plug of a primary conducting metal fill the remaining portion of the aperture. The present invention also includes methods for making the metallization structures.

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